JST3400

30V,5.8A
N-Channel Mosfet

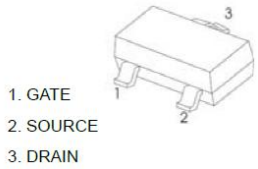
FEATURES

RDS(ON)≤ 33mΩ @VGS=10V

RDS(ON)≤ 39mΩ @VGS=4.5V

RDS(ON)≤ 60mΩ @VGS=2.5V

SOT-23



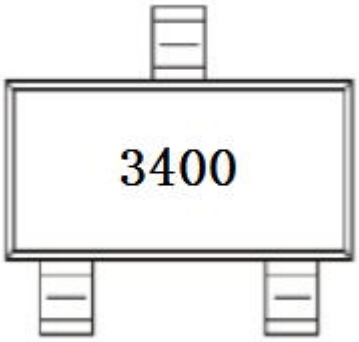
1. GATE
2. SOURCE
3. DRAIN

APPLICATIONS

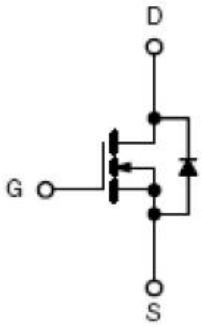
Load/Power Switching

Interfacing Switching

MARKING



N-CHANNEL MOSFET



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current	I_D	5.8	A
Pulsed Drain Current	I_{DM}	30	
Maximum Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient(t ≤5s)	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 ~+150	

MOSFET ELECTRICAL CHARACTERISTICS T_a=25 ℃ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	30	31.5		V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.7	1	1.4	
Gate-source leakage	I_{GSS}	V_{DS} =0V, V_{GS} =±12V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} =30V, V_{GS} =0V			1	μA
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} =10V, I_D =5A		21	33	mΩ
		V_{GS} =4.5V, I_D =4A		25	39	
		V_{GS} =2.5V, I_D =3A		36	60	
Body diode voltage	V_{SD}	I_S=1A		0.8	1	V
Dynamic[b]						
Input capacitance	C_{iss}	V_{DS} =15V,V_{GS} =0V,f =1MHz			1155	pF
Output capacitance	C_{oss}			108		
Reverse transfer capacitance	C_{rss}			84		
Total gate charge	Q_g	V_{DS} =15V,V_{GS} =4.5V,I_D =5.8A		10		nC
Gate-source charge	Q_{gs}			1.6		
Gate-drain charge	Q_{gd}			3.1		
Turn-on delay time	$t_{d(on)}$	V_{DD}=15V,R_L=2.7Ω, V_{GS}=10V,R_{GEN}=3Ω			5	nS
Rise time	t_r				7	
Turn-off delay time	$t_{d(off)}$				40	
Fall time	t_f				6	

Notes :

a. Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.

b. Guaranteed by design, not subject to production testing.

N-Channel 30V (D-S) MOSFET Typical Characteristics

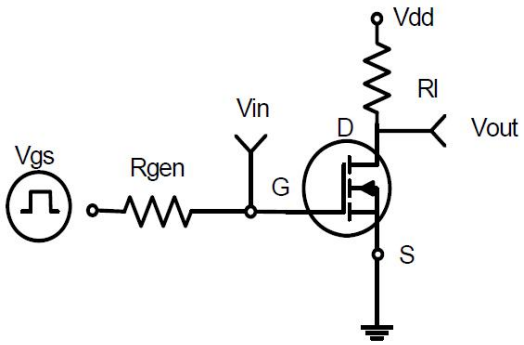


Figure 1:Switching Test Circuit

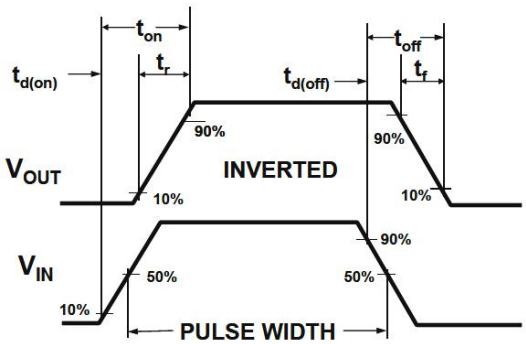


Figure 2:Switching Waveforms

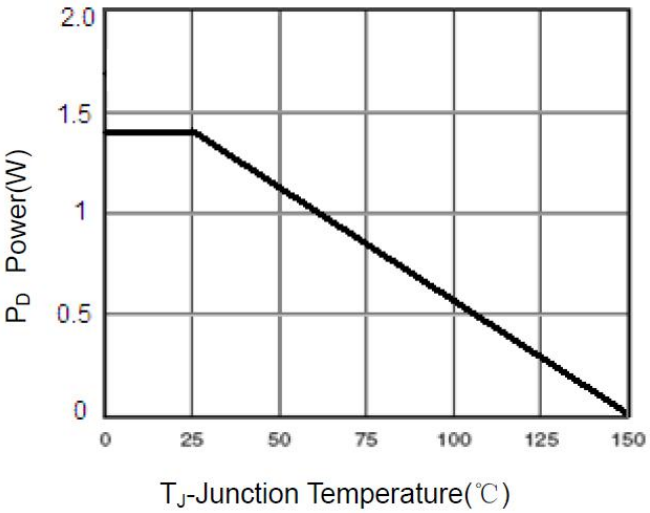


Figure 3 Power Dissipation

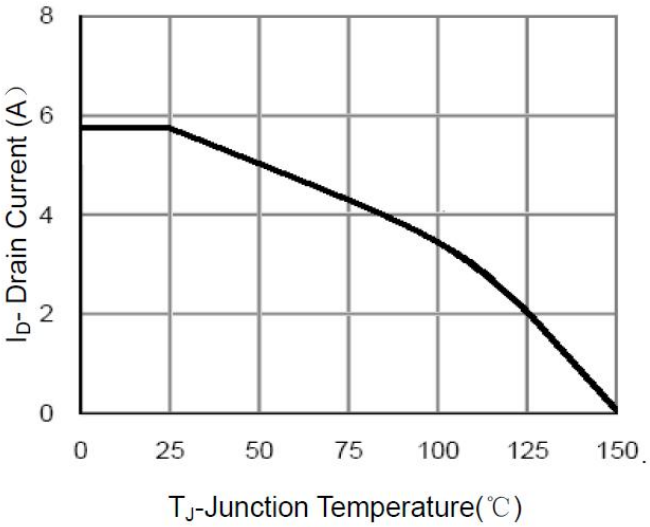


Figure 4 Drain Current

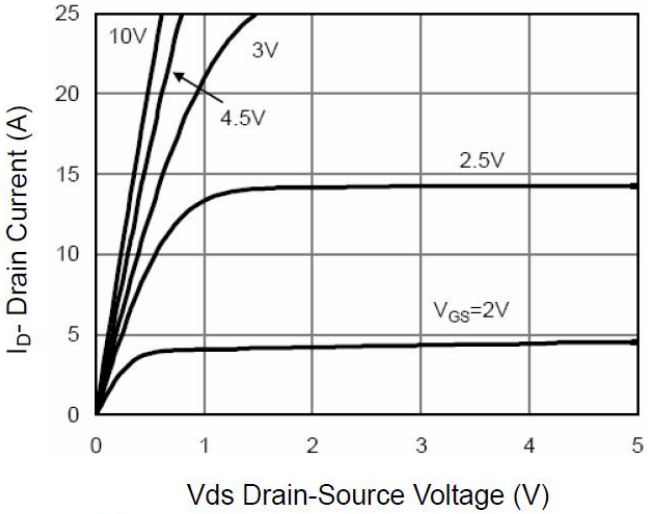


Figure 5 Output Characteristics

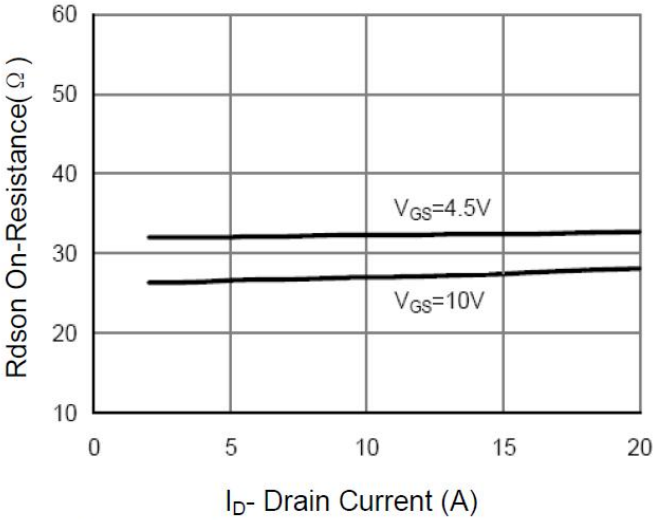


Figure 6 Drain-Source On-Resistance

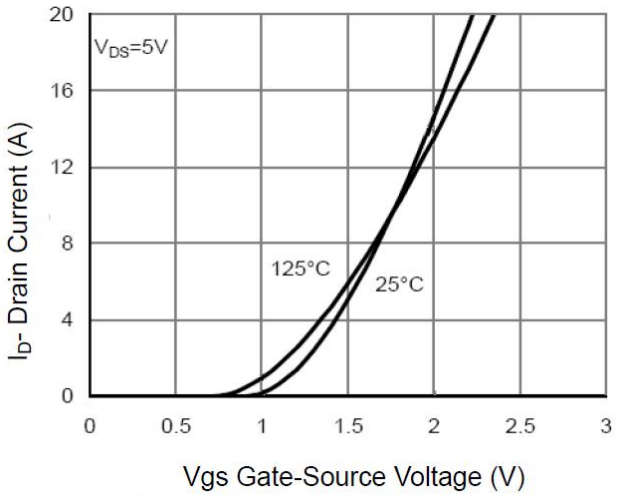


Figure 7 Transfer Characteristics

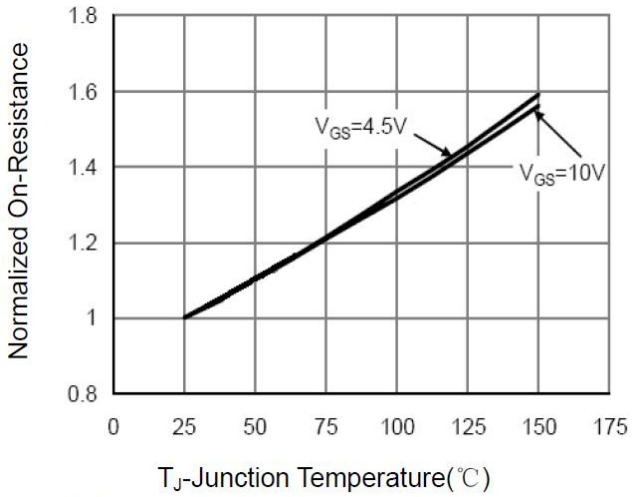


Figure 8 Drain-Source On-Resistance

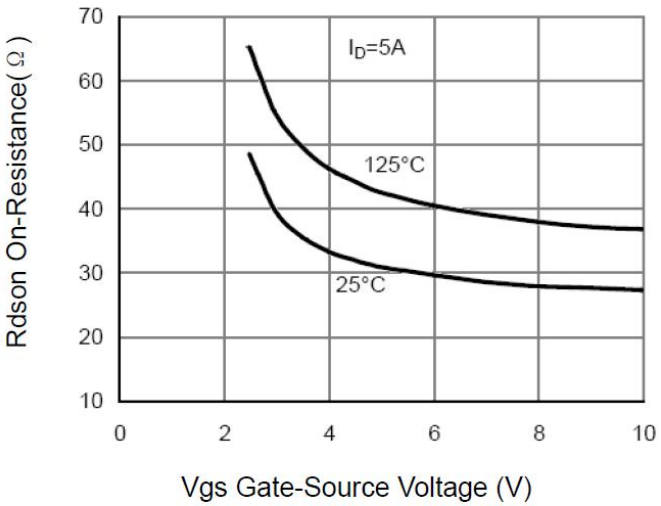


Figure 9 Rdson vs Vgs

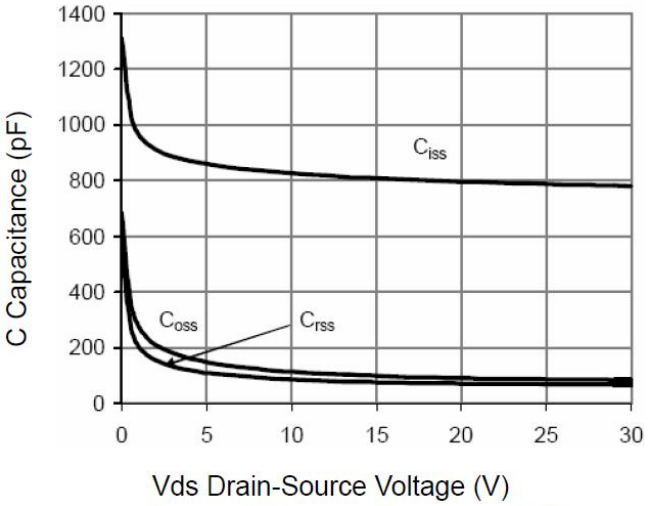


Figure 10 Capacitance vs Vds

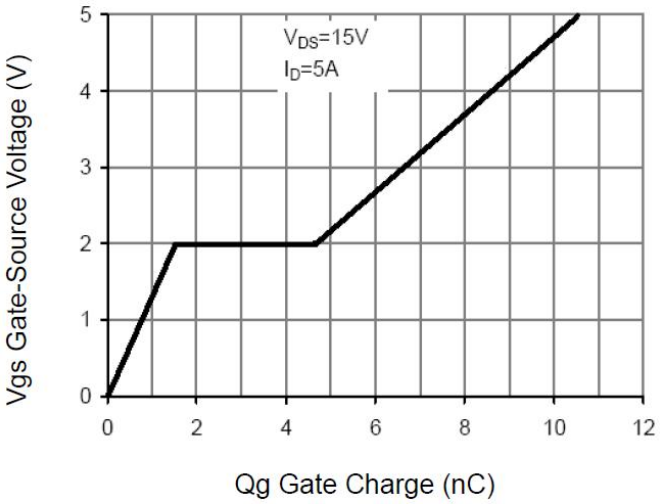


Figure 11 Gate Charge

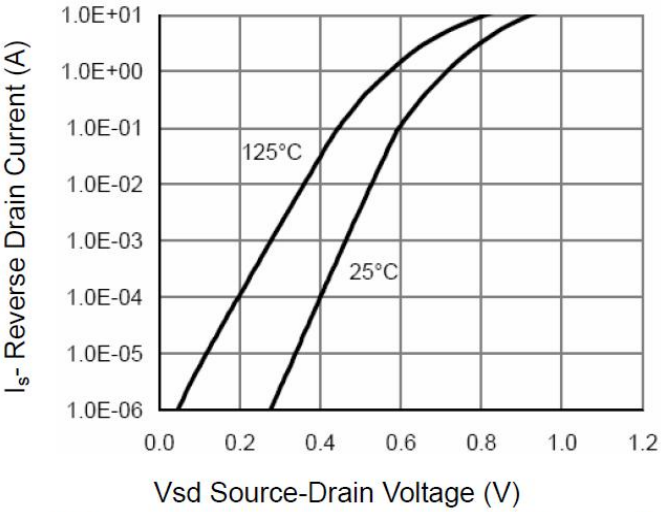
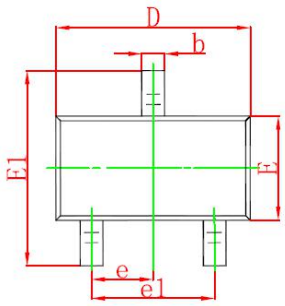
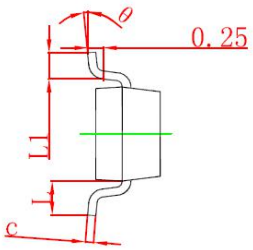
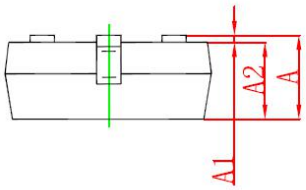


Figure 12 Source- Drain Diode Forward

SOT-23 package

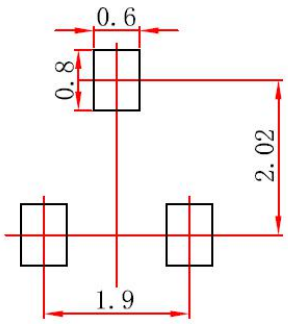






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.